



# Thyristor \ Diode Module

$V_{RRM} = 2 \times 1200 \text{ V}$

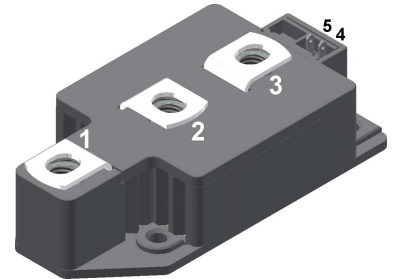
$I_{TAV} = 320 \text{ A}$

$V_T = 1.08 \text{ V}$

Phase leg

Part number

**MCD310-12io1**



Backside: isolated



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: Y2

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

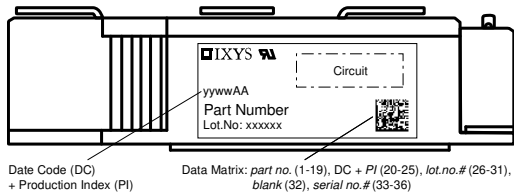
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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}C$		1	mA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 140^{\circ}C$		40	mA
$V_T$	forward voltage drop	$I_T = 300\text{ A}$	$T_{VJ} = 25^{\circ}C$		1.14	V
		$I_T = 600\text{ A}$			1.32	V
		$I_T = 300\text{ A}$	$T_{VJ} = 125^{\circ}C$		1.08	V
		$I_T = 600\text{ A}$			1.30	V
$I_{TAV}$	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		320	A
$I_{T(RMS)}$	RMS forward current	180° sine			500	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0.80	V
$r_T$	slope resistance				0.82	mΩ
$R_{thJC}$	thermal resistance junction to case				0.11	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.04		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		1030	W
$I_{TSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		9.20	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		9.94	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		7.82	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		8.45	kA
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		423.2	kA <sup>2</sup> s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		410.6	kA <sup>2</sup> s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		305.8	kA <sup>2</sup> s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		296.7	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400\text{ V } f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		438	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}C$		120	W
		$t_p = 500\text{ }\mu\text{s}$			60	W
$P_{GAV}$	average gate power dissipation				20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50\text{ Hz}$ repetitive, $I_T = 960\text{ A}$			100	A/ $\mu\text{s}$
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 320\text{ A}$			500	A/ $\mu\text{s}$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 140^{\circ}C$		1000	V/ $\mu\text{s}$
$V_{GT}$	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		2	V
			$T_{VJ} = -40^{\circ}C$		3	V
$I_{GT}$	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0.25	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}C$		200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$				
$I_H$	holding current	$V_D = 6\text{ V } R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu\text{s}$
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$				
$t_q$	turn-off time	$V_R = 100\text{ V}; I_T = 320\text{ A}; V = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s } dv/dt = 50\text{ V}/\mu\text{s } t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 125^{\circ}C$		200	$\mu\text{s}$



Package Y2			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				255		g
$M_D$	mounting torque		2.5		5	Nm
$M_T$	terminal torque		12		15	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	13.0			mm
$d_{Spb/Apb}$		terminal to backside	13.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD310-12io1	MCD310-12io1	Box	2	428787

**Equivalent Circuits for Simulation**

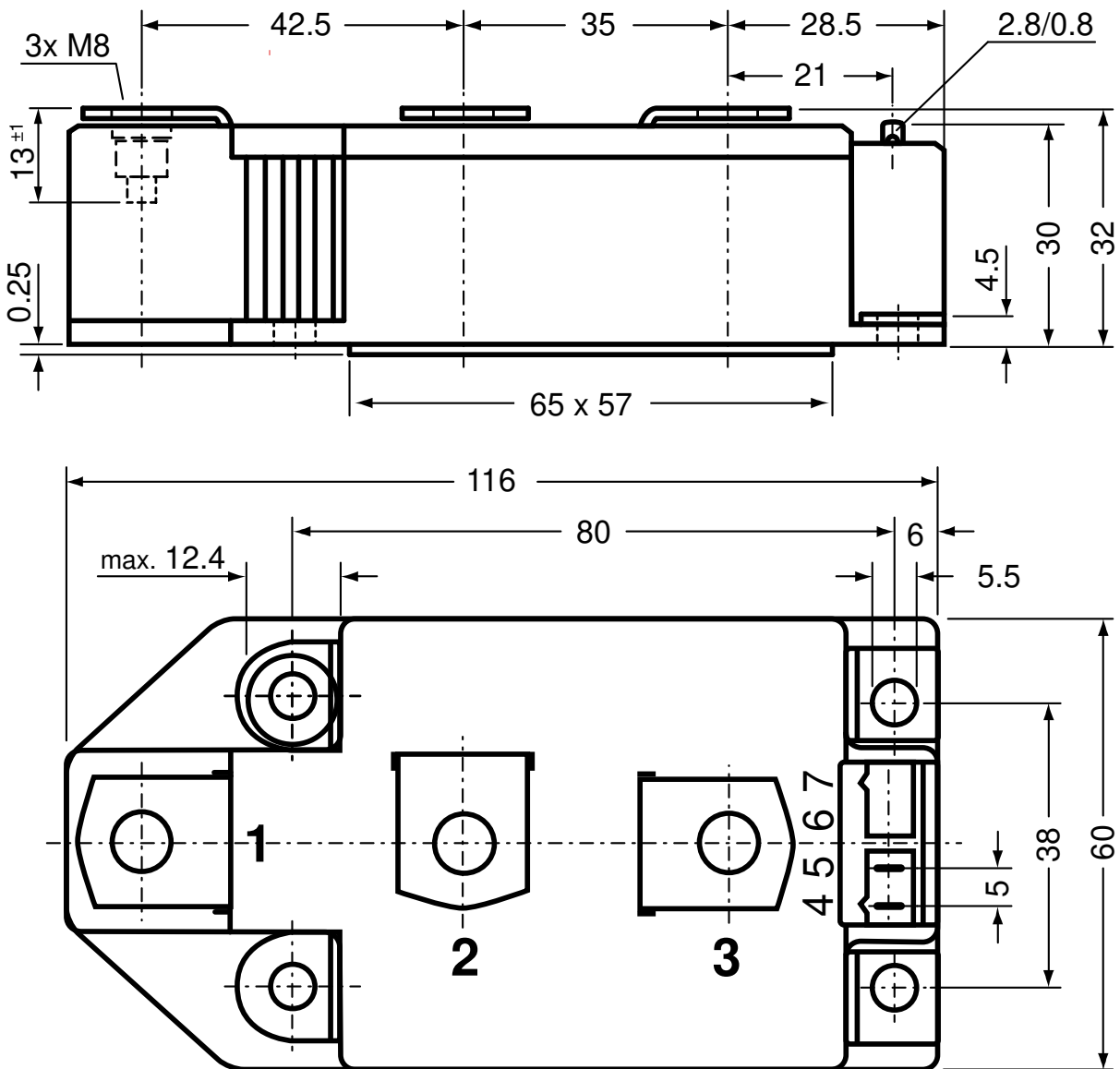
\* on die level

$T_{VJ} = 140^{\circ}C$



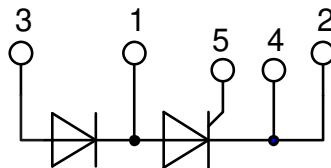
**Thyristor**

$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	0.32	mΩ

**Outlines Y2**


Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
 Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751





**Thyristor**

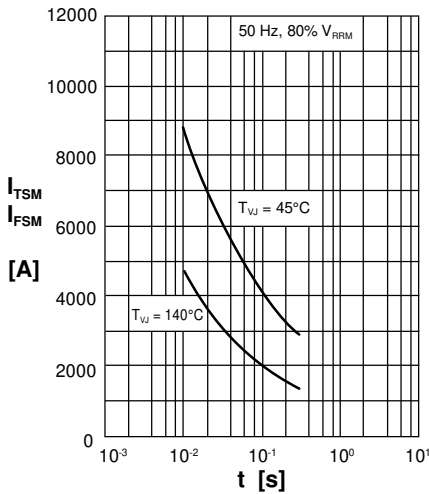


Fig. 1 Surge overload current  
 $I_{T(F)SM}$ : crest value, t: duration

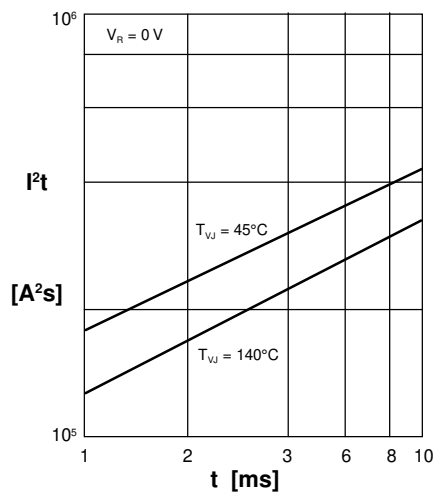


Fig. 2  $I^2t$  versus time (1-10 ms)

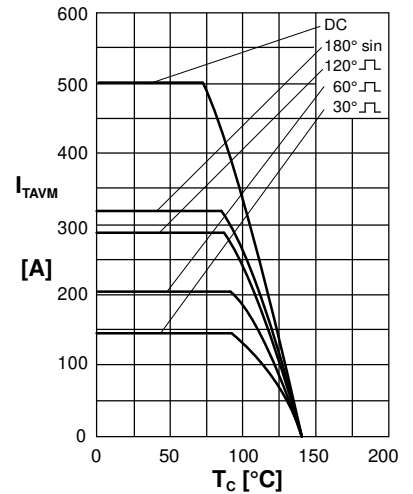


Fig. 3 Max. forward current at case temperature

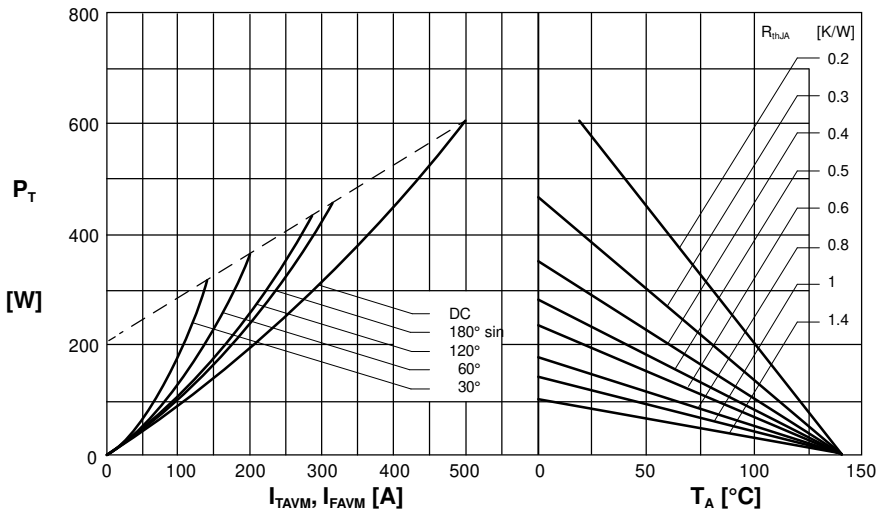


Fig. 4 Power dissipation versus onstate current and ambient temperature (per thyristor/diode)

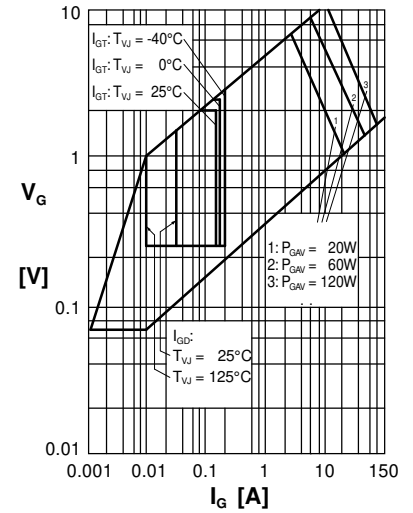


Fig. 5 Gate trigger characteristics

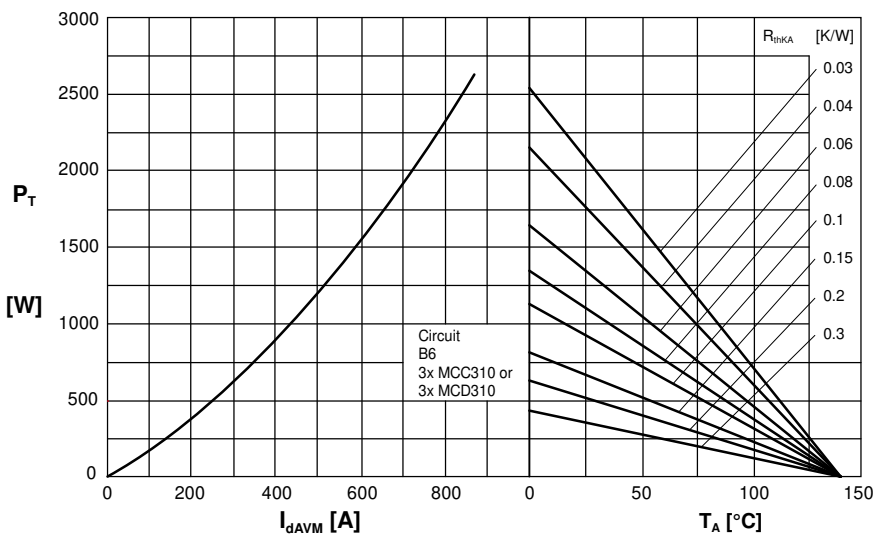


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

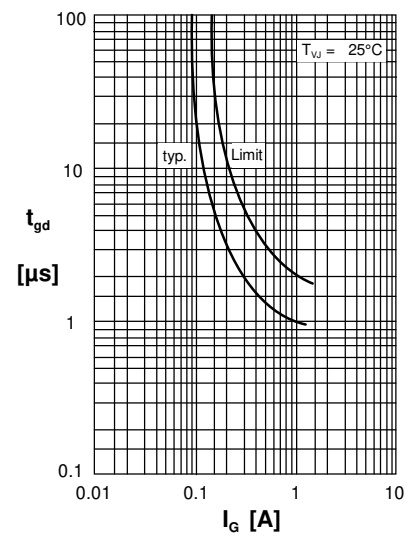


Fig. 7 Gate trigger delay time



**Rectifier**

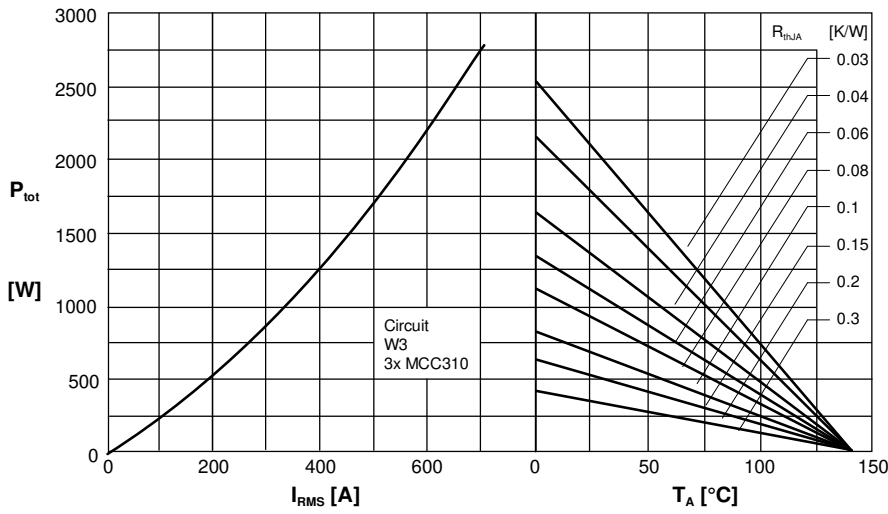


Fig. 7 Three phase AC-controller: • Power dissipation versus RMS output current and ambient temperature

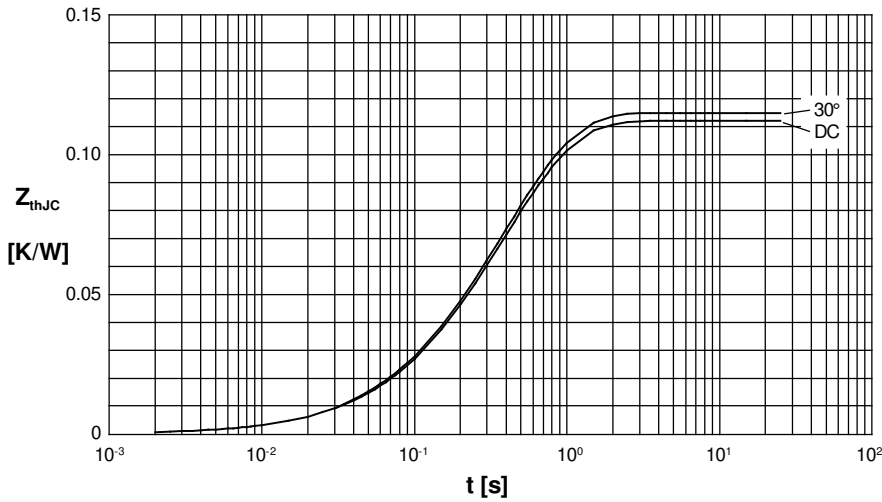


Fig. 8 Transient thermal impedance junction to case (per thyristor)

$R_{\theta JC}$  for various conduction angles d:

d	$R_{\theta JC}$ (K/W)
DC	0.112
180°C	0.113
120°C	0.114
60°C	0.115
30°C	0.115

Constants for  $Z_{\theta JC}$  calculation:

i	$R_{\theta i}$ [K/W]	$t_i$ [s]
1	0.003	0.099
2	0.0143	0.168
3	0.0947	0.456

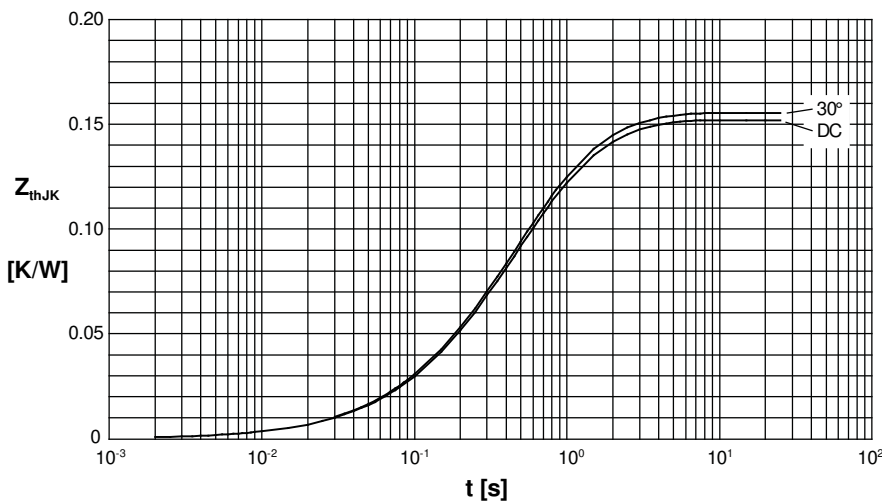


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

$R_{\theta JK}$  for various conduction angles d:

d	$R_{\theta JK}$ [K/W]
DC	0.152
180°C	0.154
120°C	0.154
60°C	0.155
30°C	0.155

Constants for  $Z_{\theta JK}$  calculation:

i	$R_{\theta i}$ (K/W)	$t_i$ (s)
1	0.003	0.099
2	0.0143	0.168
3	0.0947	0.456
4	0.04	1.36